

10/031117

L Number	Hits	Search Text	DB	Time stamp
1	89553	non-volatile or nonvolatile near5 memor\$3	USPAT; US-PGPUB; JPO	2003/06/10 10:21
2	18309	float\$3 near3 gate\$1	USPAT; US-PGPUB; JPO	2003/06/10 10:22
3	56191	control near2 gate\$1	USPAT; US-PGPUB; JPO	2003/06/10 10:22
4	25443	select\$3 near2 gate\$1	USPAT; US-PGPUB; JPO	2003/06/10 10:22
5	95088	polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon))	USPAT; US-PGPUB; JPO	2003/06/10 10:23
6	4383	(non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))	USPAT; US-PGPUB; JPO	2003/06/10 10:23
7	1754026	source\$1 or drain\$1	USPAT; US-PGPUB; JPO	2003/06/10 10:23
8	4175	((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)	USPAT; US-PGPUB; JPO	2003/06/10 10:24
9	301054	etch\$3	USPAT; US-PGPUB; JPO	2003/06/10 10:24
10	132929	implant\$3	USPAT; US-PGPUB; JPO	2003/06/10 10:24
11	1948	((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3	USPAT; US-PGPUB; JPO	2003/06/10 10:24
12	750	(((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (select\$3 near2 gate\$1)	USPAT; US-PGPUB; JPO	2003/06/10 10:26
27	3543	eras\$3 near2 gate\$1	USPAT; US-PGPUB; JPO	2003/06/10 12:16
28	161024	polish\$3 or cmp	USPAT; US-PGPUB; JPO	2003/06/10 12:17
29	750	(((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (select\$3 near2 gate\$1)	USPAT; US-PGPUB; JPO	2003/06/10 12:17
30	634	(((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)	USPAT; US-PGPUB; JPO	2003/06/10 12:17
31	309	(((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)) not (((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (select\$3 near2 gate\$1))	USPAT; US-PGPUB; JPO	2003/06/10 12:17

32	61	(polish\$3 or cmp) and ((((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)) not ((((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (select\$3 near2 gate\$1)))	USPAT; US-PGPUB; JPO	2003/06/10 12:17
33	248	(((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)) not ((((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (select\$3 near2 gate\$1))) not ((polish\$3 or cmp) and ((((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (eras\$3 near2 gate\$1)) not ((((((non-volatile or nonvolatile near5 memor\$3) and (float\$3 near3 gate\$1) and (control near2 gate\$1) and (polysilicon or polysi or poly-si or (polycrystalline adj (si or silicon)))))) and (source\$1 or drain\$1)) and etch\$3 and implant\$3) and (select\$3 near2 gate\$1))))	USPAT; US-PGPUB; JPO	2003/06/10 12:22